

# Atomic layer deposition of ZnO films on graphene grown on SiC (0001)

S. I. Boyadjiev<sup>1</sup>

P. M. Rafailov<sup>1</sup>, V. B. Mehandjiev<sup>1</sup>, B. S. Blagoev<sup>1</sup>, K. Kirilov<sup>2</sup>, R. Yakimova<sup>3</sup>

<sup>1</sup>Georgi Nadjakov Institute of Solid State Physics, Bulgarian Academy of Sciences, Blvd. Tzarigradsko Chausse 72, 1784 Sofia, Bulgaria

<sup>2</sup>Faculty of Physics, Sofia University, 5 J. Bourchier Blvd., Sofia 1164, Bulgaria

<sup>3</sup>Department of Physics, Chemistry and Biology-IFM, Linköping University, S-58183 Linköping, Sweden  
boiajiev@gmail.com

## Abstract

Graphene films were grown on the Si-terminated face of 4H-SiC (0001). Subsequently, atomic layer deposition (ALD) of ZnO nanolayer was performed onto the graphene coating using Diethylzinc and DI water as precursors. The obtained samples were characterized with atomic force microscopy, x-ray photoelectron spectroscopy and scanning electron microscopy in the different stages of preparation. Raman spectroscopy was applied to characterize the influence of ZnO deposition onto the graphene coating.

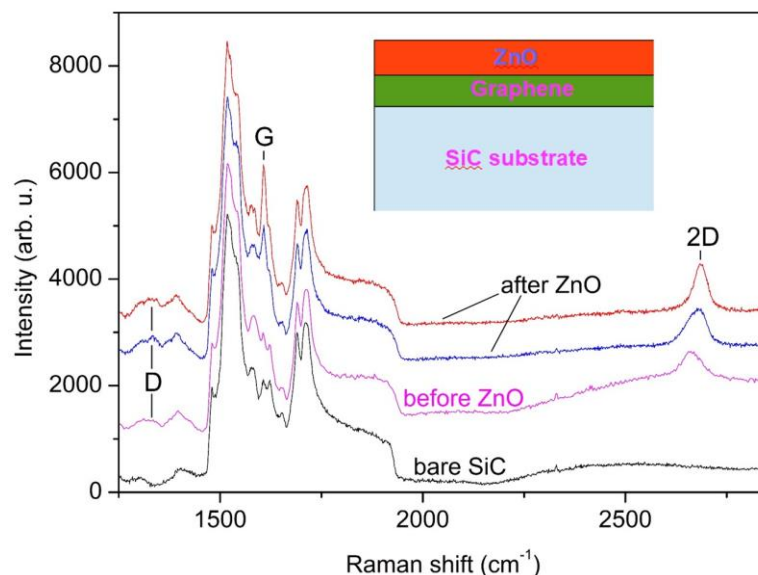
## References

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## Figures



**Figure 1:** Spectroscopic illustration of the influence of ZnO deposition on graphene grown on SiC substrate